

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claims 1-6 (cancelled)

Claim 7 (original) A method of premetal dielectric fabrication for an integrated circuit, comprising the steps of:

- (a) providing a substrate with insulated gate structures at a first surface; and
- (b) plasma-enhanced depositing a dielectric layer over said gates and substrate with a plasma-to-substrate bias initially less than a first threshold voltage but increasing to greater than a second threshold voltage which exceeds said first threshold voltage;
- (c) wherein said first threshold voltage is characterized by conformal deposition and said second threshold voltage is characterized by planarizing deposition.

Claim 8 (original) The method of claim 7, wherein:

- (a) said dielectric layer is made of silicon oxides.

Claim 9 (original) The method of claim 8, wherein:

- (a) said silicon oxides include dopants in at least a portion remote from said gate structures and substrate.

Claim 10 (original) The method of claim 8, wherein:

- (a) said silicon oxides include dopants in at least a portion adjacent said gate structures and substrate.